

March 2012 SuperFET[®] II

FCP380N60 / FCPF380N60 600V N-Channel MOSFET

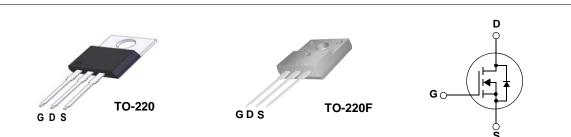
Features

- 650V @T_J = 150°C
- Max. R_{DS(on)} = 380mΩ
- Ultra low gate charge (typ. Q_g = 30nC)
- Low effective output capacitance (typ. C_{oss} .eff = 95pF)
- 100% avalanche tested

Description

SuperFET[®]II is, Fairchild's proprietary, new generation of high voltage MOSFET family that is utilizing an advanced charge balance mechanism for outstanding low on-resistance and lower gate charge performance.

This advanced technology has been tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate and higher avalanche energy. Consequently, SuperFET[®]II is very suitable for various AC/DC power conversion in switching mode operation for system miniaturization and higher efficiency.



Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter			FCP380N60	FCPF380N60	Units	
V _{DSS}	Drain to Source Voltage			600		V	
M		-DC	-DC		±20		
V _{GSS}	Gate to Source Voltage	-AC	(f>1HZ)	±30		V	
1		-Continuous (T _C = 25°C)		10.2	10.2*	•	
I _D	Drain Current	-Continuous ($T_C = 100^{\circ}C$)		6.4	6.4*	A	
I _{DM}	Drain Current	- Pulsed (Note 1)		30.6	30.6*	А	
E _{AS}	Single Pulsed Avalanche Energy (Not		(Note 2)	211.6		mJ	
I _{AR}	Avalanche Current		(Note 1)	2.3		А	
E _{AR}	Repetitive Avalanche Energy		(Note 1)) 1.06		mJ	
dv/dt	Peak Diode Recovery dv/dt (No		(Note 3)	3) 20		V/ns	
uv/ui	MOSFET dv/dt			100		v/ns	
P _D	Devues Dissischier	$(T_{C} = 25^{\circ}C)$		106	31	W	
	Power Dissipation	- Derate above 25°C		0.85	0.25	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150		°C		
TL	Maximum Lead Temperature for Soldering Purpose, 300 1/8" from Case for 5 Seconds 300			00	°C		

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FCP380N60	FCPF380N60	Units
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case	1.18	4	
$R_{\theta CS}$	Thermal Resistance, Case to Heat Sink (Typical)	0.5	0.5	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	62.5	62.5	

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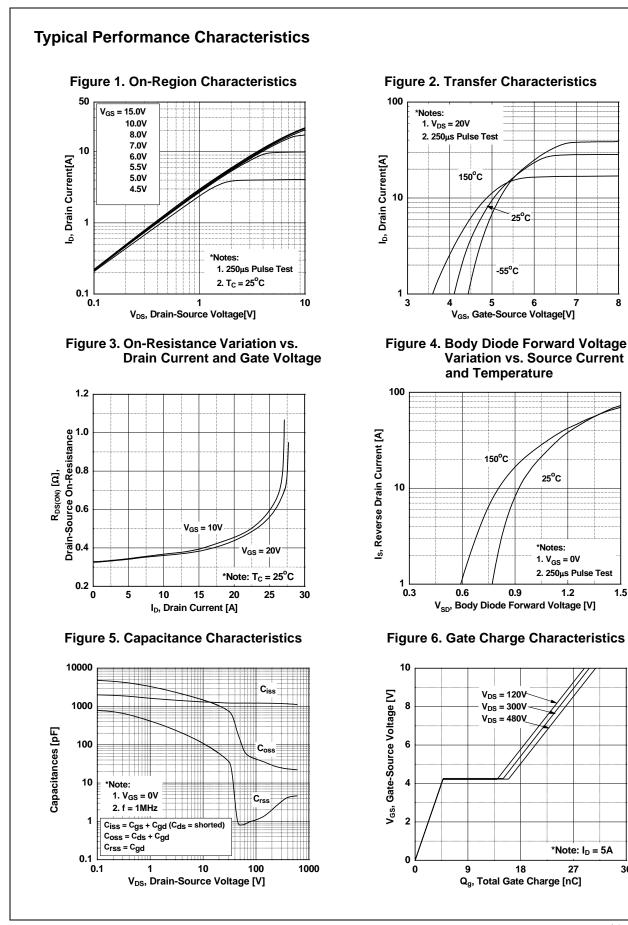
Device Marking		Device	Packag	e	Reel Size	Тар	e Width		Quantit	у
		TO-220	2	-		-		50		
FCPF380	N60	FCPF380N60	TO-220	F	-		-		50	
Electrica	I Char	acteristics T _c =	25ºC unless	otherwis	e noted					
Symbol		Parameter			Test Conditions		Min.	Тур.	Max.	Unit
Off Charac	teristic	S								
		2 2 1 1 1		V _{GS} = 0V, I _D = 10mA, T _J = 25°C		600	-	-	V	
BV _{DSS}	Drain to	Source Breakdown Vo	oltage		$V, I_D = 10 \text{mA}, T_J = 1$		650	-	-	V
ΔBV _{DSS} ΔTJ	Breakdo	own Voltage Temperatu ent	ıre	$I_D = 10$ mA, Referenced to 25°C		-	0.6	-	V/ºC	
BV _{DS}		ource Avalanche Brea	kdown	$V_{GS} = 0$	0V, I _D = 10A		-	700	-	V
Voltage				$V_{De} = 4$	480V, V _{GS} = 0V		-	-	1	
I _{DSS}	Zero Ga	ate Voltage Drain Curre	ent	-	480V, T _C = 125°C		-	-	10	μA
I _{GSS}	Gate to	o Body Leakage Current			$\pm 20V, V_{DS} = 0V$		-	-	±100	nA
	Į			00	50	ļ	ļ		Į	1
On Charac				N/	V 1 050 A		0.5		25	V
V _{GS(th)}		e Threshold Voltage		$V_{GS} = V_{DS}, I_D = 250 \mu A$		2.5	-	3.5	V	
R _{DS(on)}		Drain to Source On Resistance		$V_{GS} = 10V, I_D = 5A$ $V_{DS} = 20V, I_D = 5A$		-	0.33	0.38	Ω S	
9fs				vDS =						0
Dynamic C	haracte	eristics								
C _{iss}	Input Ca	apacitance				-	1250	1665	pF	
C _{oss}	Output (t Capacitance se Transfer Capacitance		$- V_{\text{DS}} = 25V, V_{\text{GS}} = 0V$ - f = 1MHz		-	905	1205	pF	
C _{rss}	Reverse					-	45	60	pF	
C _{oss}	Output 0	Capacitance		$V_{DS} = 380V, V_{GS} = 0V, f = 1.0MHz$		-	23	-	pF	
C _{oss} eff.	Effective	ve Output Capacitance		$V_{DS} = 0V \text{ to } 480V, V_{GS} = 0V$ $V_{DS} = 380V, I_D = 5A$ $V_{GS} = 10V$ (Note 4)		-	95	-	pF	
Q _{g(tot)}	Total Ga	Gate Charge at 10V o Source Gate Charge o Drain "Miller" Charge				-	30	40	nC	
Q _{gs}	Gate to					-	5	-	nC	
Q _{gd}						-	10	-	nC	
ESR	Equivale	ent Series Resistance		Drain Open			1		Ω	
Switching	Charac	teristics								
t _{d(on)}	Turn-On	Delay Time				-	14	38	ns	
t _r	Turn-On	-On Rise Time -Off Delay Time		$V_{DD} = 380V, I_D = 5A$ $V_{GS} = 10V, R = 4.7\Omega$ (Note 4)		-	7	24	ns	
t _{d(off)}	Turn-Off					-	45	100	ns	
t _f	Turn-Off	rn-Off Fall Time				-	6	22	ns	
Drain-Sou	ce Dior	de Characteristic	e							
I _s	1			e Forwar	d Current		-	-	10.2	A
I _{SM}		Maximum Continuous Drain to Source Diod Maximum Pulsed Drain to Source Diode Fo				-	-	30.6	A	
V _{SD}		ain to Source Diode Forward Voltage		$V_{GS} = 0V, I_{SD} = 5A$		-	-	1.2	V	
t _{rr}		Recovery Time	30		$V, I_{SD} = 5A$		-	240	-	ns
Q _{rr}					= 100A/μs	F	-	2.7	-	μC
A ll	11010100	erse Recovery Charge					2		μΟ	

 $\begin{array}{l} 3. \ I_{SD} \leq 5.1 A, \ di/dt \leq 200 A/\mu s, \ V_{DD} \leq B V_{DSS}, \ Starting \ T_J = 25^\circ C \\ 4. \ Essentially Independent of Operating Temperature Typical Characteristics \end{array}$

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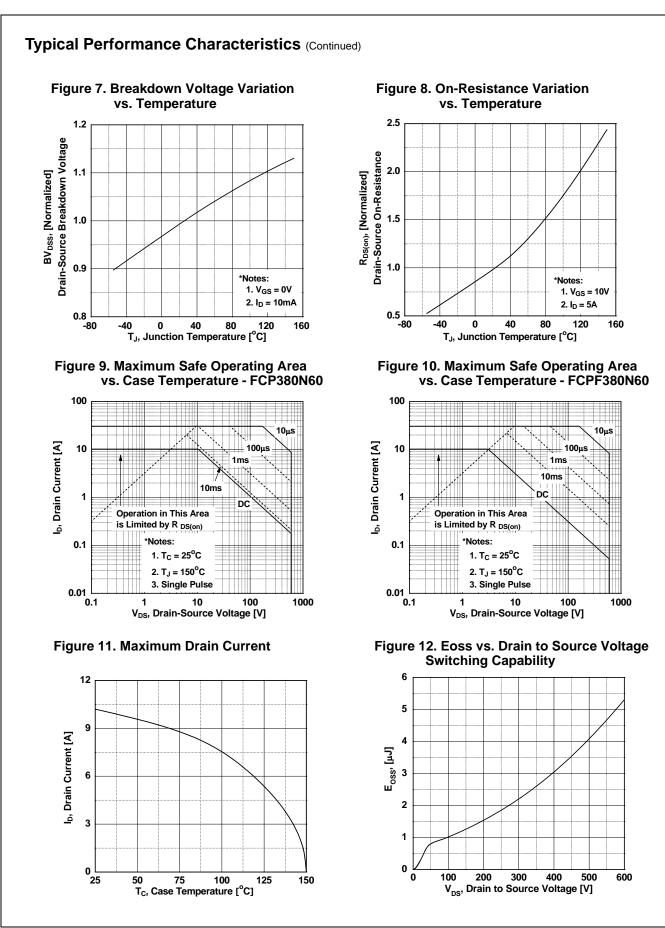
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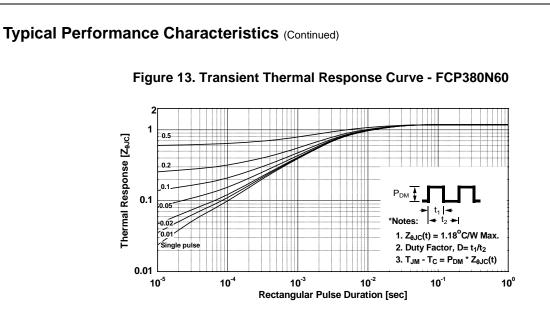
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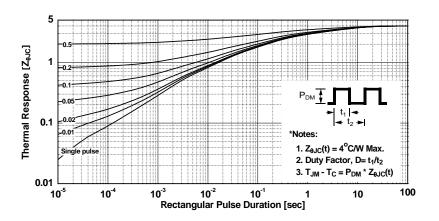
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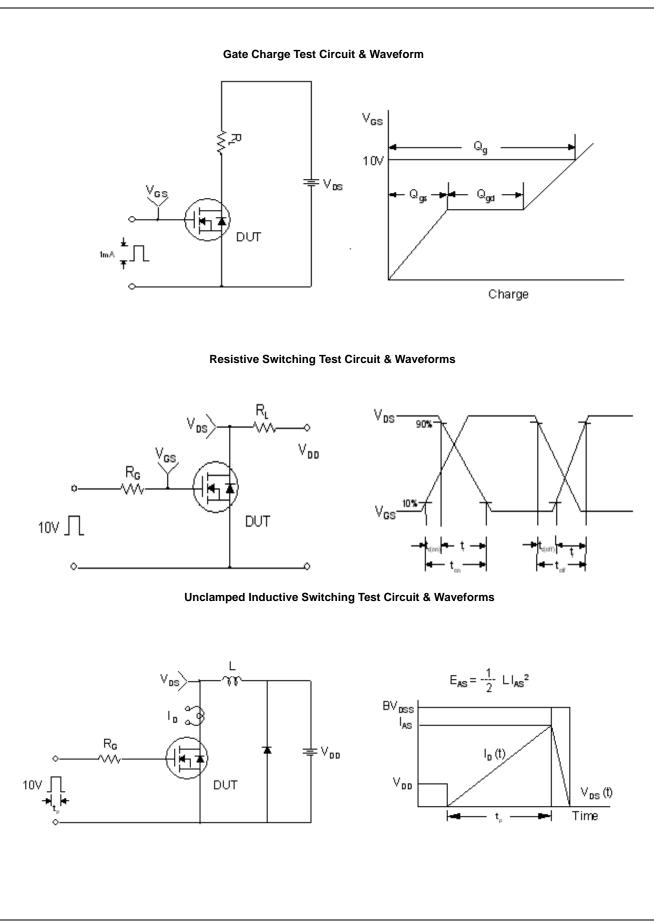






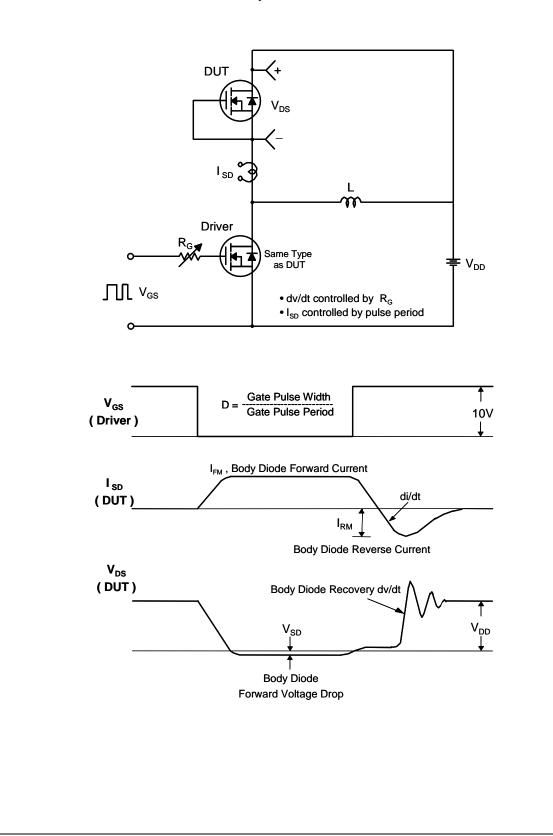


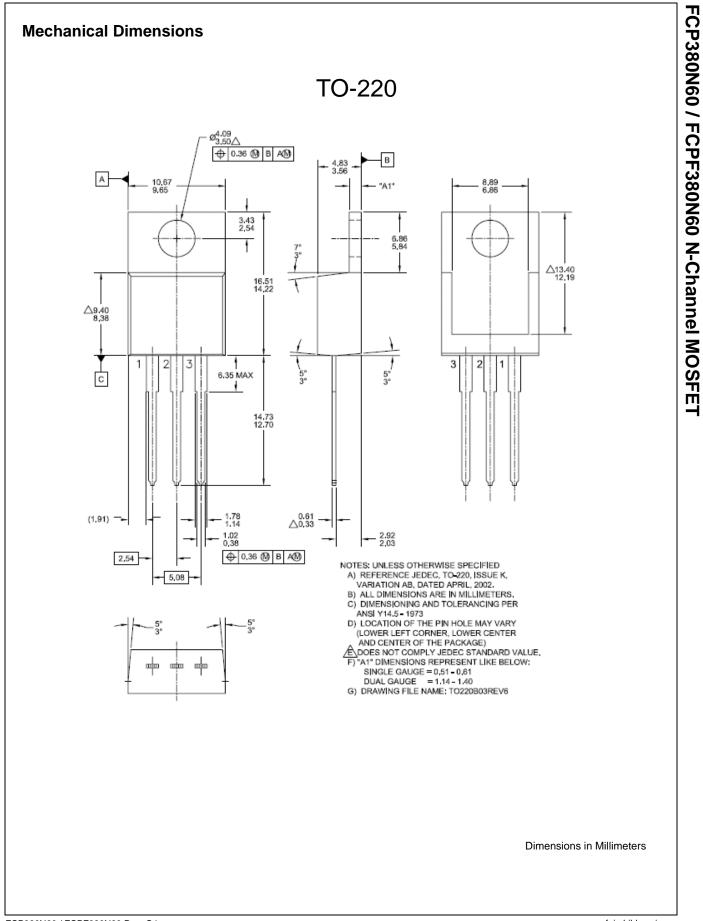


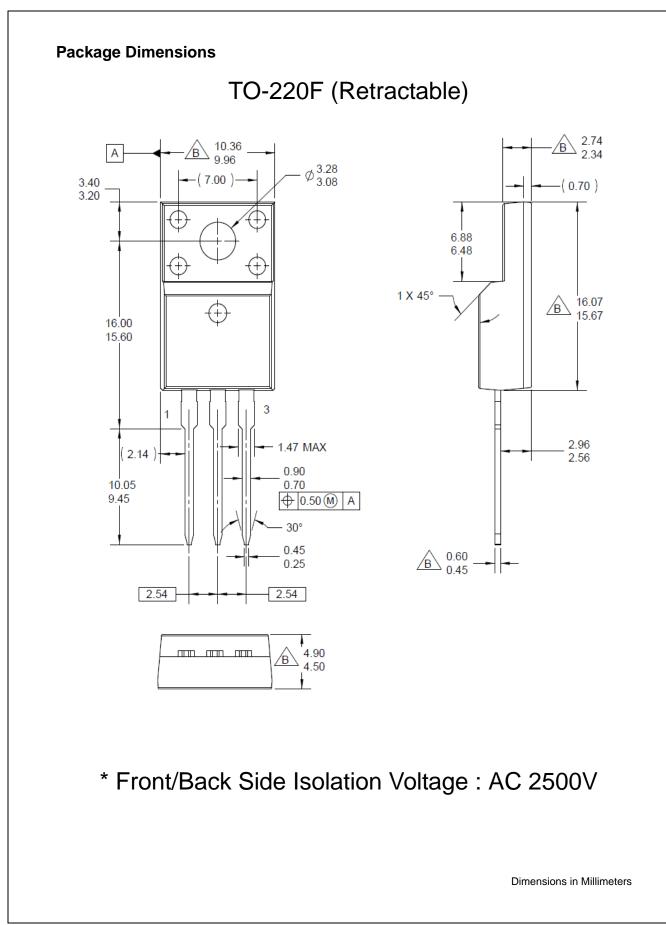


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Peak Diode Recovery dv/dt Test Circuit & Waveforms









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